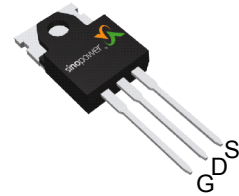


N-Channel Enhancement Mode MOSFET

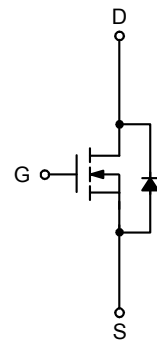
Features

- 80V/83A,
 $R_{DS(ON)} = 9.6m\Omega$ (max.) @ $V_{GS} = 10V$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

Pin Description



Top View of TO-220H

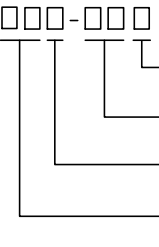


N-Channel MOSFET

Applications

- Switching Application

Ordering and Marking Information

SM7580NS □□□-□□□  Assembly Material Handling Code Temperature Range Package Code	Package Code FH : TO-220H Operating Junction Temperature Range C : -55 to 150 °C Handling Code TU : Tube (50ea/tube) Assembly Material G : Halogen and Lead Free Device
SM7580NS FH :  SM7580N XXXXX	XXXXX - Lot Code

Note: SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		80	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	83	A
I _{DP}	300µs Pulse Drain Current Tested	T _C =25°C	200	
I _D	Continuous Drain Current	T _C =25°C	83	
		T _C =100°C	52	
P _D	Maximum Power Dissipation	T _C =25°C	113	W
		T _C =100°C	45	
R _{θJC}	Thermal Resistance-Junction to Case		1.1	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		62.5	
E _{AS}	Avalanche Energy, Single Pulsed	L=2mH	460	mJ

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0\text{V}, I_{\text{DS}} = 250\mu\text{A}$	80	-	-	V
$\Delta BV_{\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	$V_{\text{GS}} = 0\text{V}, I_{\text{DS}} = 250\mu\text{A}$	-	0.073	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 60\text{V}, V_{\text{GS}} = 0\text{V}$	-	-	1	μA
		$T_J = 85^\circ\text{C}$	-	-	30	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{DS}} = 250\mu\text{A}$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{\text{GS}} = \pm 25\text{V}, V_{\text{DS}} = 0\text{V}$	-	-	± 100	nA
$R_{\text{DS(ON)}}^a$	Drain-Source On-state Resistance	$V_{\text{GS}} = 10\text{V}, I_{\text{DS}} = 40\text{A}$	-	8	9.6	$\text{m}\Omega$
Diode Characteristics						
V_{SD}^a	Diode Forward Voltage	$I_{\text{SD}} = 20\text{A}, V_{\text{GS}} = 0\text{V}$	-	0.8	1.3	V
t_{rr}	Reverse Recovery Time	$I_{\text{SD}} = 40\text{A},$	-	41	-	ns
Q_{rr}	Reverse Recovery Charge	$di_{\text{SD}}/dt = 100\text{A}/\mu\text{s}$	-	71	-	nC

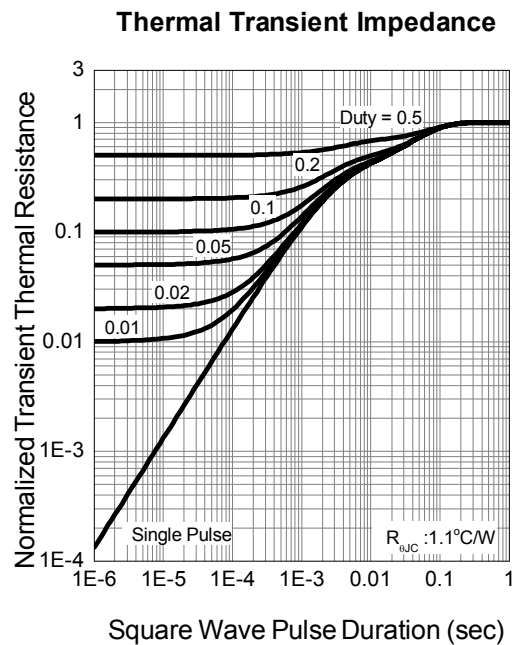
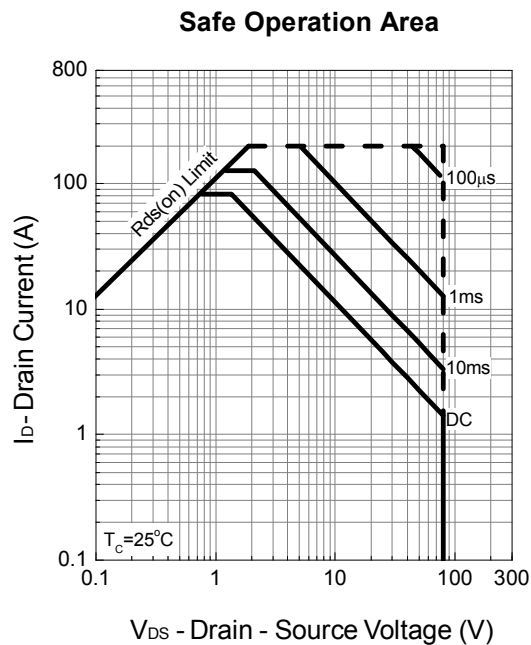
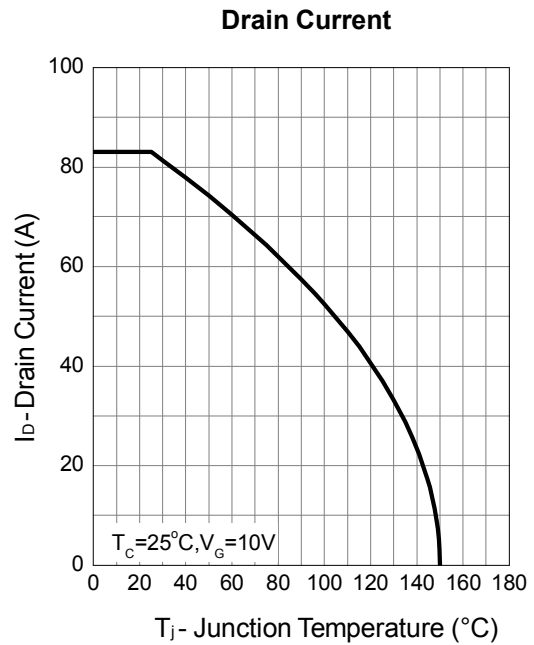
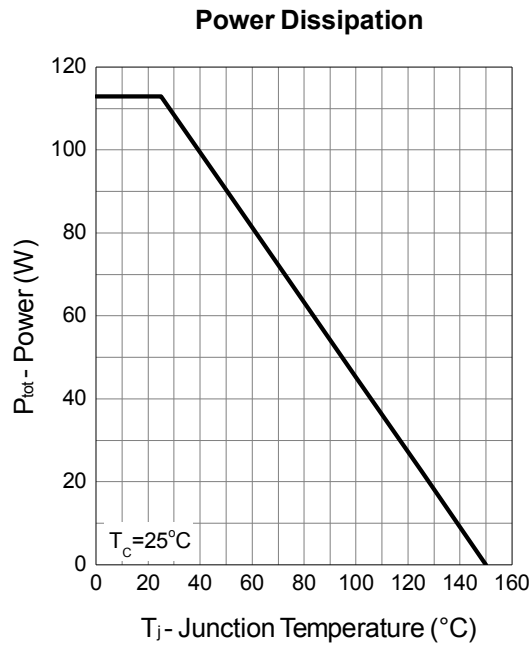
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	4460	6240	pF
C _{oss}	Output Capacitance		-	362	-	
C _{rss}	Reverse Transfer Capacitance		-	276	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	23	41	ns
t _r	Turn-on Rise Time		-	16	29	
t _{d(OFF)}	Turn-off Delay Time		-	75	135	
t _f	Turn-off Fall Time		-	38	68	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =40V, V _{GS} =10V, I _{DS} =40A	-	89	125	nC
Q _{gs}	Gate-Source Charge		-	23	-	
Q _{gd}	Gate-Drain Charge		-	26	-	

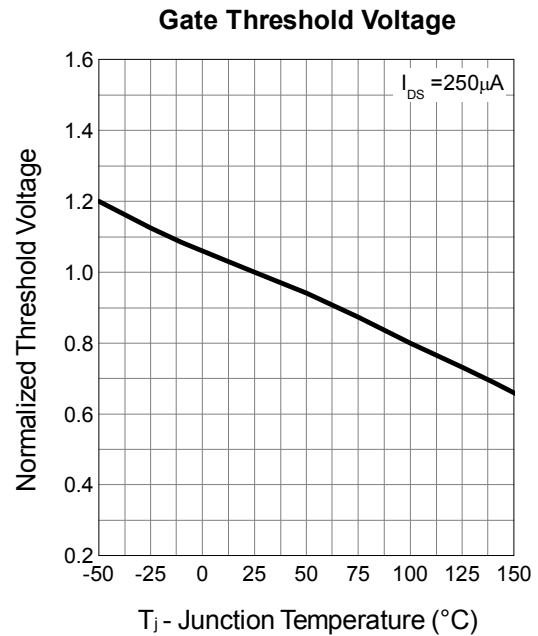
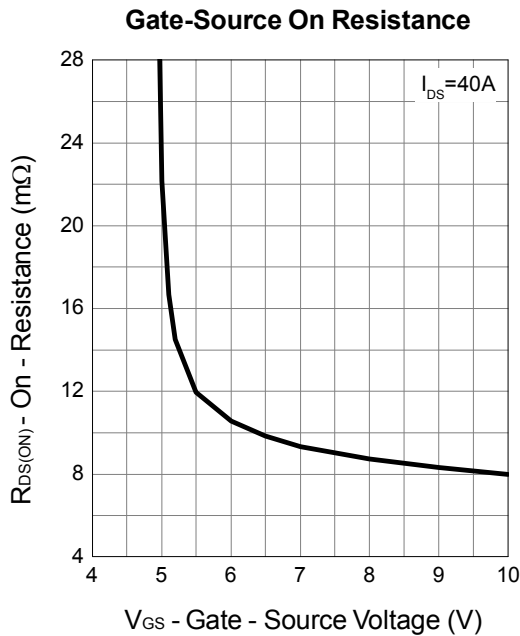
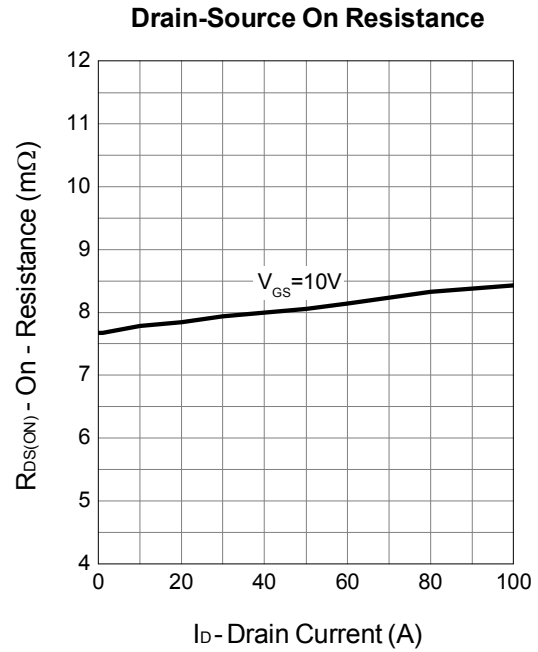
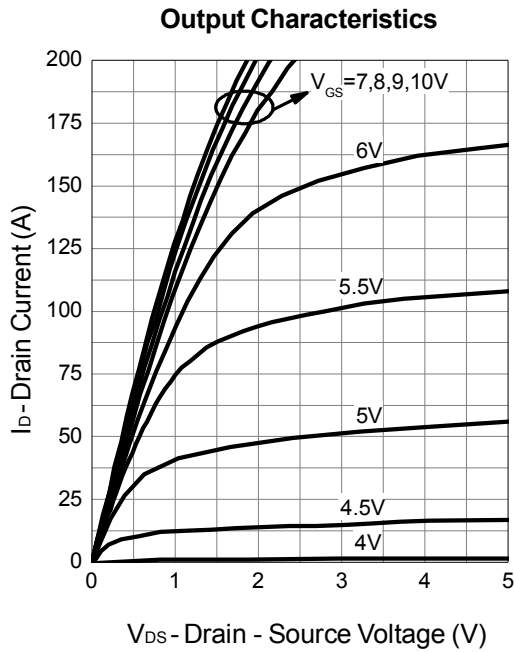
Note a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

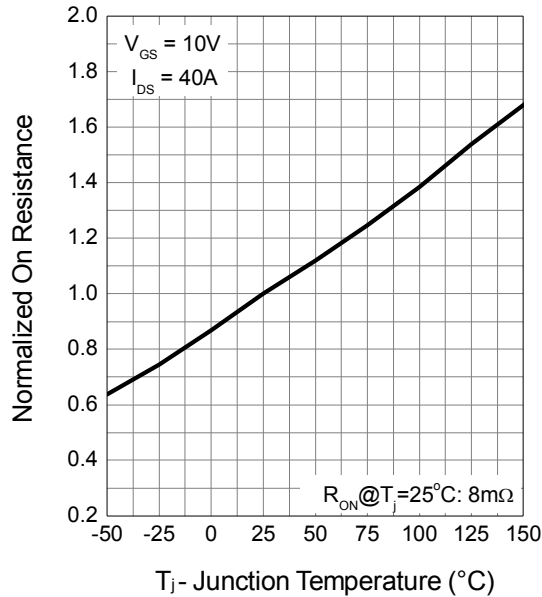


Typical Operating Characteristics (Cont.)

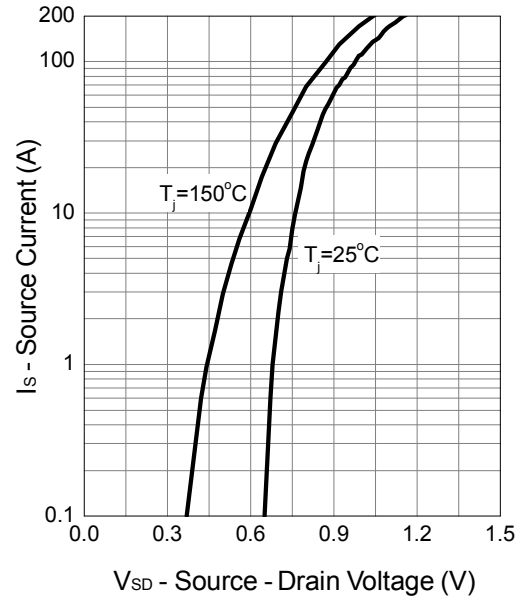


Typical Operating Characteristics (Cont.)

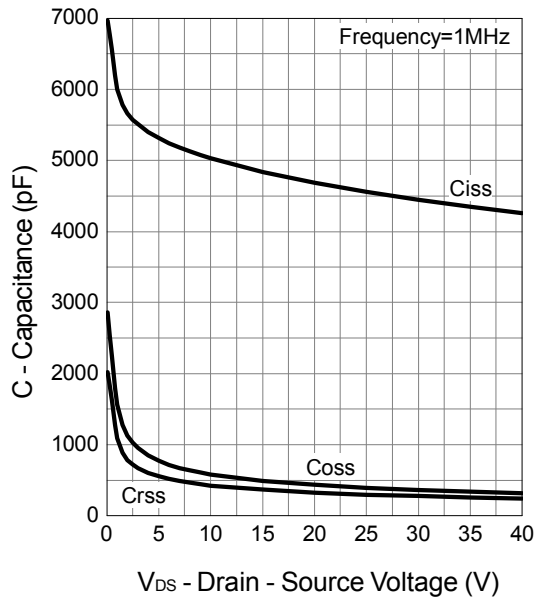
Drain-Source On Resistance



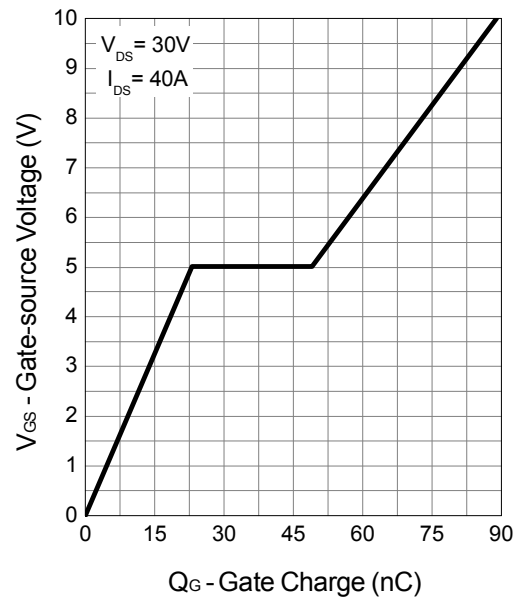
Source-Drain Diode Forward



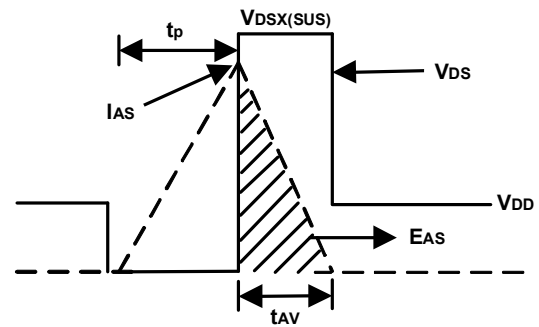
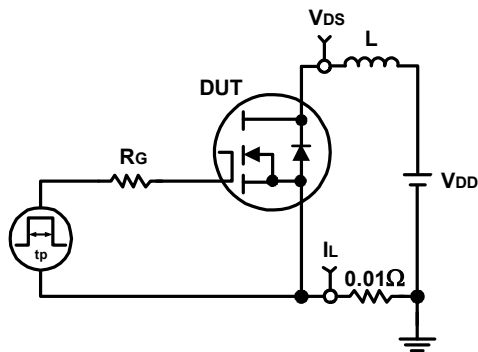
Capacitance



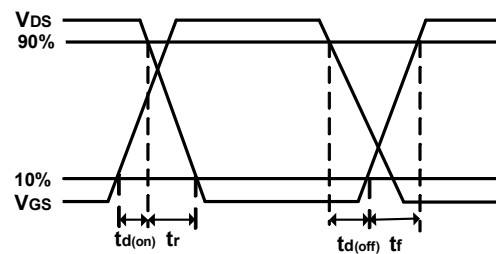
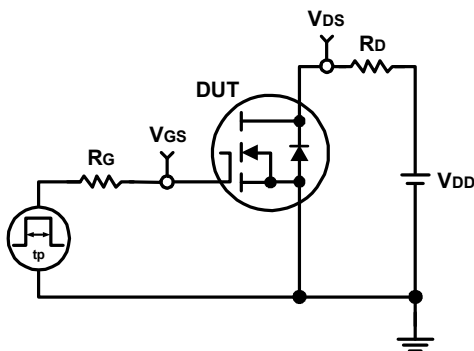
Gate Charge



Avalanche Test Circuit and Waveforms

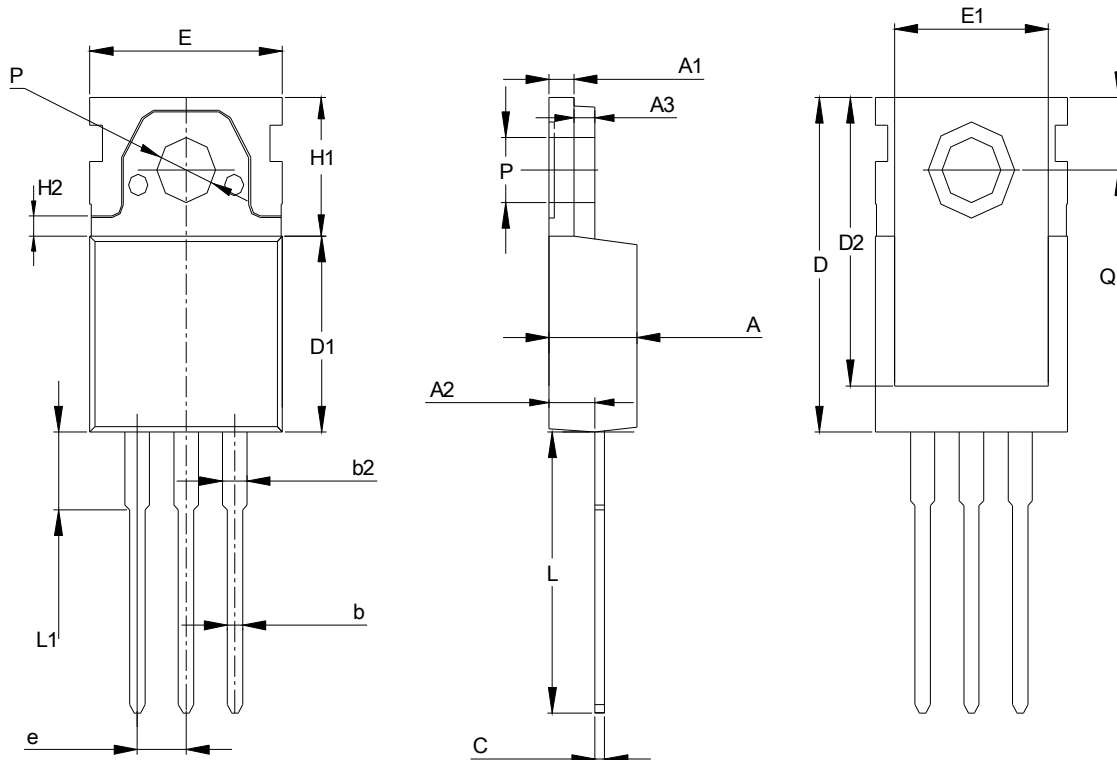


Switching Time Test Circuit and Waveforms



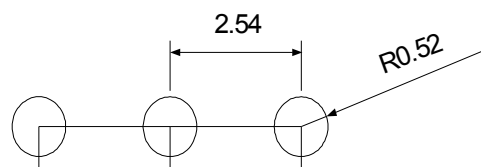
Package Information

TO-220H



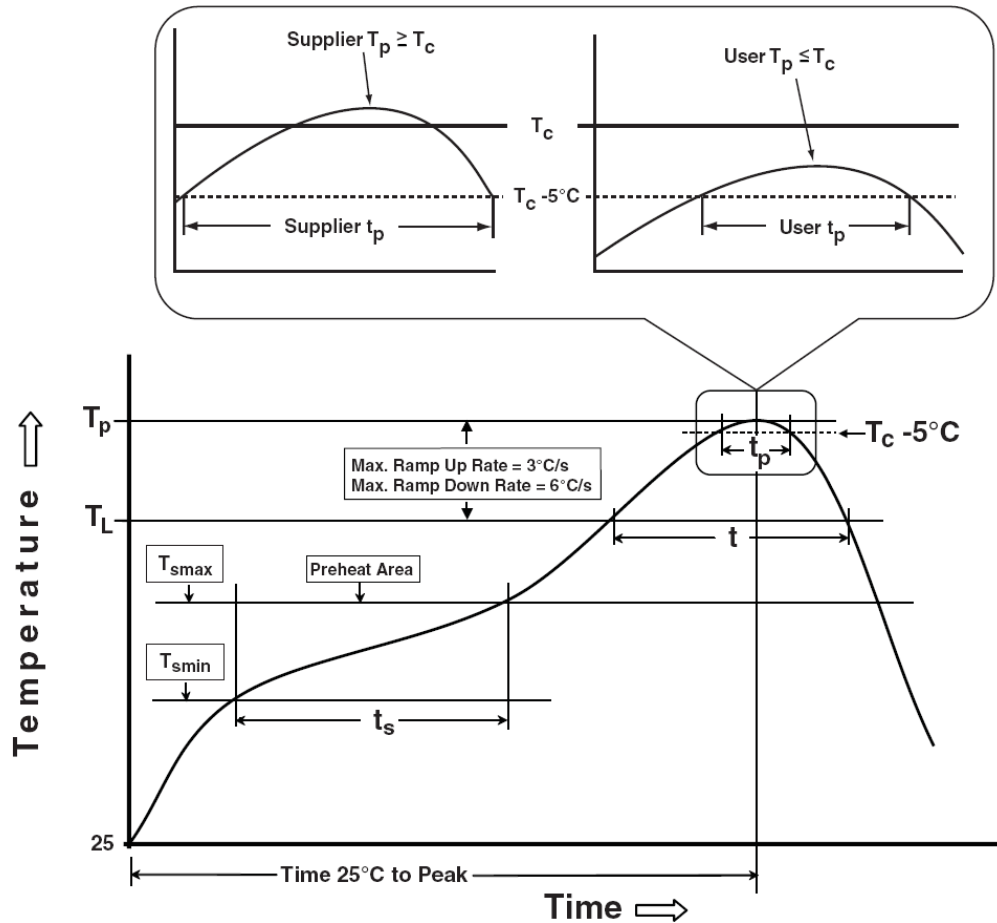
SYMBOL	TO-220H			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	3.56	4.83	0.140	0.190
A1	0.51	1.50	0.020	0.059
A2	2.03	2.92	0.080	0.115
A3	1.05	1.15	0.041	0.045
b	0.38	1.02	0.015	0.040
b2	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.22	16.51	0.560	0.650
D1	8.38	9.30	0.330	0.366
D2	12.19	13.65	0.480	0.537
E	9.65	10.67	0.380	0.420
E1	6.86	8.89	0.270	0.350
e	2.54 BSC		0.100 BSC	
H1	5.84	6.86	0.230	0.270
H2	0.95	1.05	0.037	0.041
L	12.70	14.73	0.500	0.580
L1	-	6.35	-	0.250
P	3.00	3.20	0.118	0.126
Q	3.30	3.50	0.130	0.138

RECOMMENDED LAND PATTERN



UNIT: mm

Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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